

November 1999 ADVANCE INFORMATION

FDZ2551N Dual N-Channel 2.5V Specified PowerTrench[™] BGA MOSFET

General Description

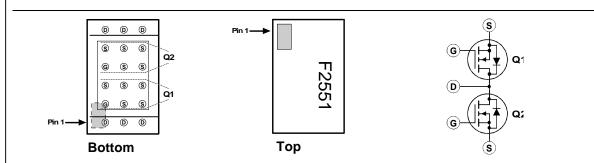
Combining Fairchild's advanced 2.5V specified PowerTrench process with state of the art BGA packaging, the FDZ2551N minimizes both PCB space and $R_{DS(ON)}$. This dual BGA MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, high current handling capability, ultralow profile packaging, low gate charge, and low $R_{DS(ON)}$.

Applications

- Battery management
- Load switch
- Battery protection

Features

- 9 A, 20 V. $\begin{array}{l} {\sf R}_{\sf DS(ON)} = 0.018 \; \Omega \; @ \; {\sf V}_{\sf GS} = 4.5 \; {\sf V} \\ {\sf R}_{\sf DS(ON)} = 0.030 \; \Omega \; @ \; {\sf V}_{\sf GS} = 2.5 \; {\sf V}. \end{array}$
- Occupies only 0.10 cm² of PCB area. 1/3 the area of SO-8.
- Ultra-thin package: less than 0.70 mm height when mounted to PCB.
- Outstanding thermal transfer characteristics: significantly better than SO-8.
- Ultra-low Q_g x R_{DS(ON)} figure-of-merit.
- High power and current handling capability.



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter			Ratings U	
V _{DSS}	Drain-Source Voltag	je		20	V
V _{GSS}	Gate-Source Voltag	e		±12	V
D	Drain Current – Co	ontinuous	(Note 1a)	9	A
	– Pi	ulsed		20	
P _D	Power Dissipation (Steady State)	(Note 1a)	3	W
	Operating and Storage Junction Temperature Range				
		0	mperature Range	-55 to +175	⊃°C
T _J , T _{stg} Therma	Operating and Stora	0	mperature Range	-55 to +175	⊃°C
Therma R _{eja}	I Characterist	ics , Junction-to-Am	nbient (Note 1a)	-55 to +175 50	°C/W
Therma R _{0JA}	I Characterist	ics , Junction-to-Am	nbient (Note 1a)		°C/W
Therma R _{θJA} R _{θJC}	I Characterist Thermal Resistance Thermal Resistance e Marking and Marking	iCS , Junction-to-Am , Junction-to-Ca	nbient (Note 1a) ISE (Note 1)	50	

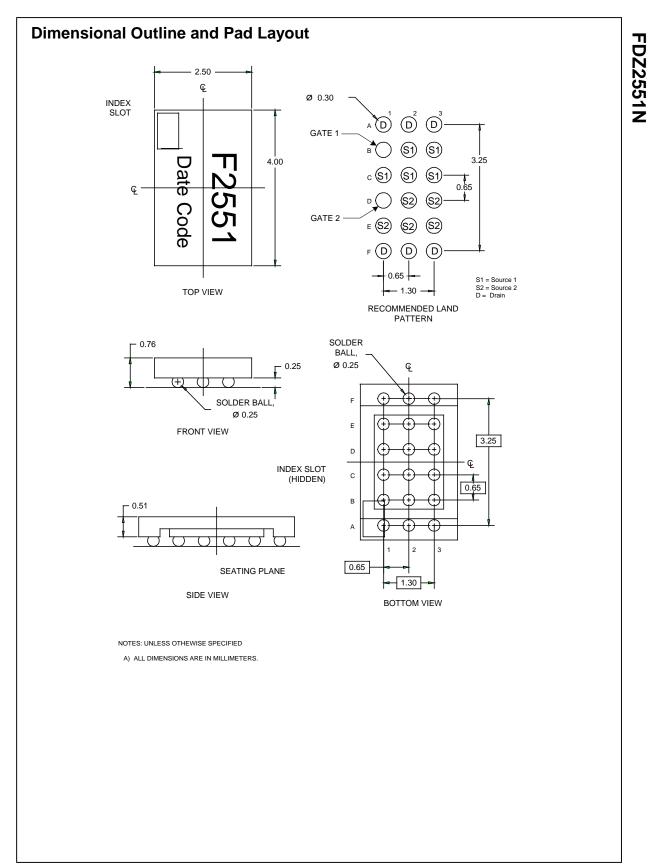
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FDZ2551N

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	20			V
ΔBV_{DSS} ΔT_{J}	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		14		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16 V$, $V_{GS} = 0 V$			1	μA
I _{GSSF}	Gate–Body Leakage Current, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate–Body Leakage Current, Reverse	$V_{GS} = -12 \text{ V} \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_{D} = 250 \ \mu A$	0.4	0.9	1.5	V
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{array}{c} V_{DS} = V_{GS}, \ I_D = 250 \ \mu A \\ V_{GS} = 4.5 \ V, \qquad I_D = 9 \ A \\ V_{GS} = 2.5 \ V, \qquad I_D = 7 \ A \end{array}$			0.018 0.030	Ω
Drain-Se	ource Diode Characteristics	and Maximum Ratings		1		L
ls	Maximum Continuous Drain–Source Diode Forward Current 2.5 A				Α	
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 2.5 A$ (Note 2)		0.77	1.2	V

(a). $R_{_{\theta JA}}$ = 50°C/W (steady-state) when mounted on 1 in^2 of 2 oz. copper.

2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%



FDZ2551N Rev A(W)

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